



# HMBTA94

PNP EPITAXIAL PLANAR TRANSISTOR

## Description

The HMBTA94 is designed for application that requires high voltage.

## Features

- High Breakdown Voltage:  $V_{CEO}=400(\text{Min.})$  at  $I_C=1\text{mA}$
- Complementary to HMBTA44

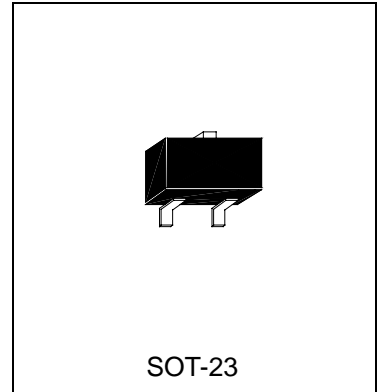
## Absolute Maximum Ratings

- Maximum Temperatures  
Storage Temperature ..... -55 ~ +150 °C  
Junction Temperature ..... +150 °C Maximum
- Maximum Power Dissipation  
Total Power Dissipation ( $T_a=25^\circ\text{C}$ ) ..... 350 mW
- Maximum Voltages and Currents ( $T_a=25^\circ\text{C}$ )  
VCBO Collector to Base Voltage ..... -400 V  
VCEO Collector to Emitter Voltage ..... -400 V  
VEBO Emitter to Base Voltage ..... -6 V  
IC Collector Current ..... -150 mA

## Characteristics ( $T_a=25^\circ\text{C}$ )

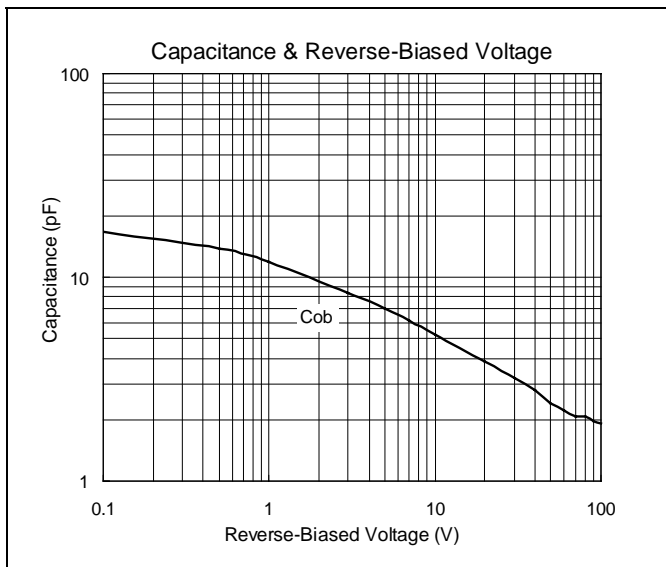
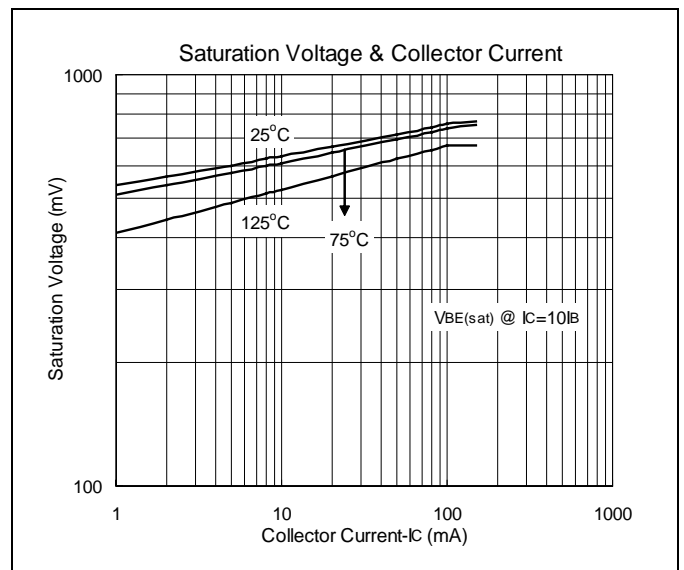
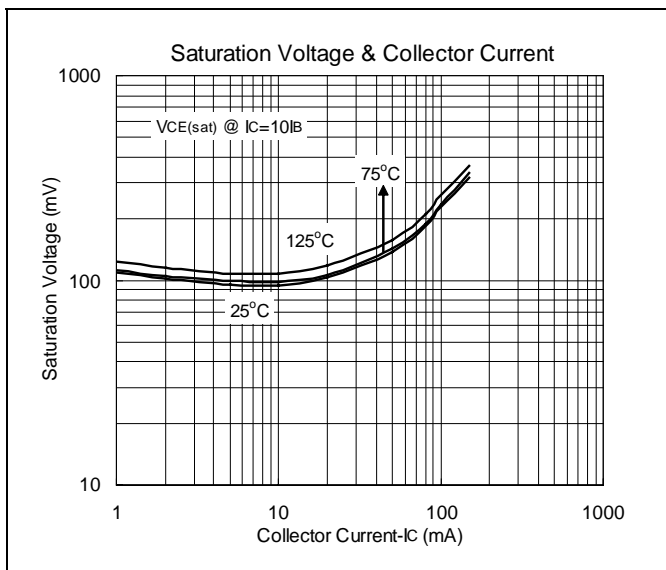
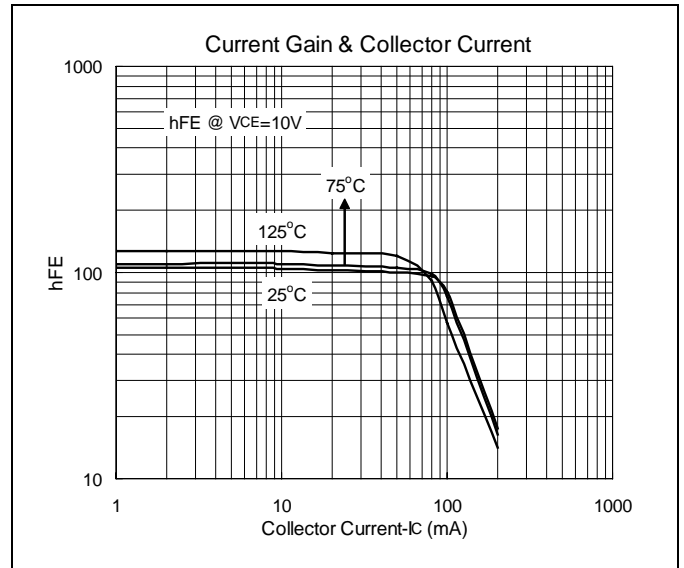
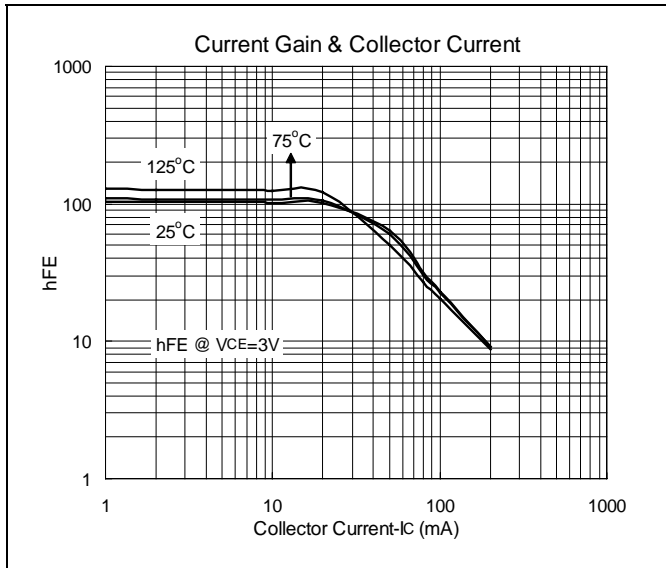
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-400	-	-	V	$I_C=-100\mu\text{A}$ , $I_E=0$
BVCEO	-400	-	-	V	$I_C=-1\text{mA}$ , $I_B=0$
BVEBO	-6	-	-	V	$I_E=-10\mu\text{A}$ , $I_C=0$
ICBO	-	-	-100	nA	$V_{CB}=-400\text{V}$ , $I_E=0$
IEBO	-	-	-100	nA	$V_{EB}=-6\text{V}$ , $I_C=0$
ICES	-	-	-500	nA	$V_{CE}=-400\text{V}$ , $V_{BE}=0$
*VCE(sat)1	-	-	-200	mV	$I_C=-1\text{mA}$ , $I_B=-0.1\text{mA}$
*VCE(sat)2	-	-	-300	mV	$I_C=-10\text{mA}$ , $I_B=-1\text{mA}$
*VCE(sat)3	-	-	-600	mV	$I_C=-50\text{mA}$ , $I_B=-5\text{mA}$
*VBE(sat)	-	-	-900	mV	$I_C=-10\text{mA}$ , $I_B=-1\text{mA}$
*hFE1	50	-	-		$V_{CE}=-10\text{V}$ , $I_C=-1\text{mA}$
*hFE2	75	-	200		$V_{CE}=-10\text{V}$ , $I_C=-10\text{mA}$
*hFE3	60	-	-		$V_{CE}=-10\text{V}$ , $I_C=-50\text{mA}$
*hFE4	40	-	-		$V_{CE}=-10\text{V}$ , $I_C=-100\text{mA}$
Cob	-	4	6	pF	$V_{CE}=-10\text{V}$ , $f=1\text{MHz}$

\*Pulse Test: Pulse Width  $\leq 380\mu\text{s}$ , Duty Cycle  $\leq 2\%$



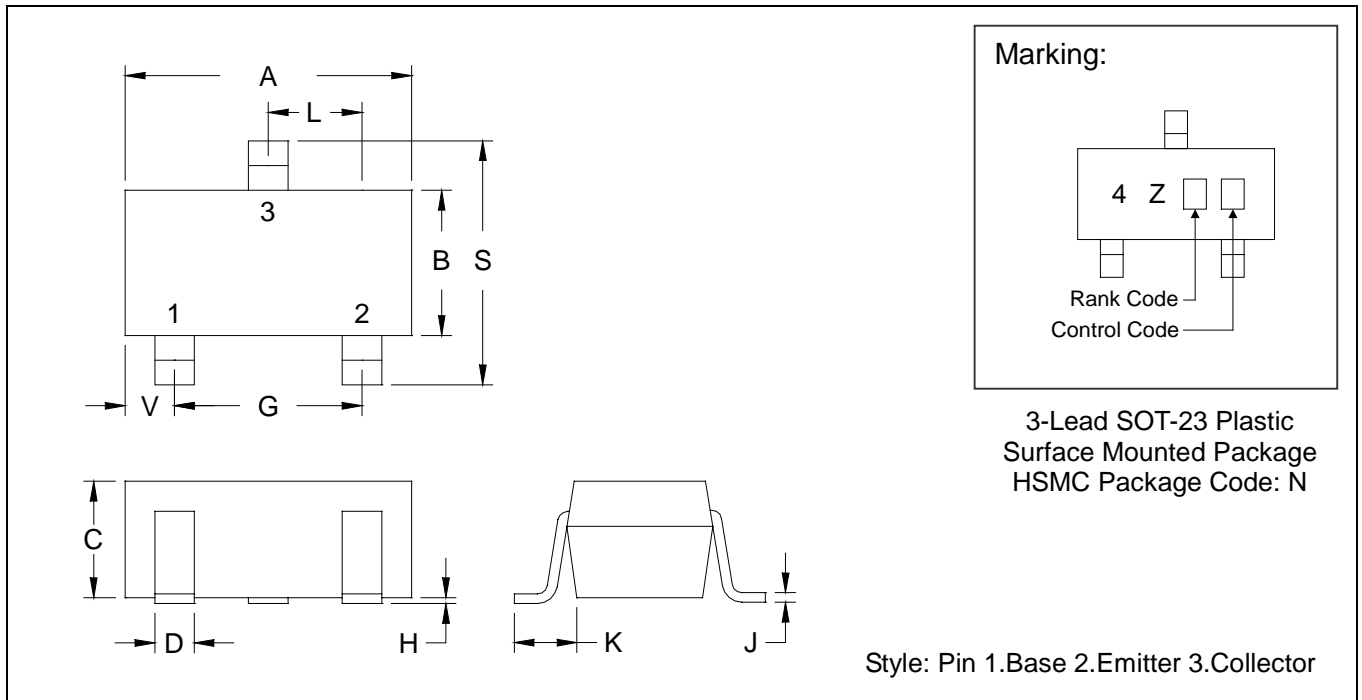


### Characteristics Curve





### SOT-23 Dimension



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

- Notes: 1.Dimension and tolerance based on our Spec. dated Sep. 07,1997.  
 2.Controlling dimension: millimeters.  
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

**Material:**

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

**Important Notice:**

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of HSMC.
- HSMC reserves the right to make changes to its products without notice.
- **HSMC semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- HSMC assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

**Head Office And Factory:**

- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F.,No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.  
 Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C  
 Tel: 886-3-5983621~5 Fax: 886-3-5982931